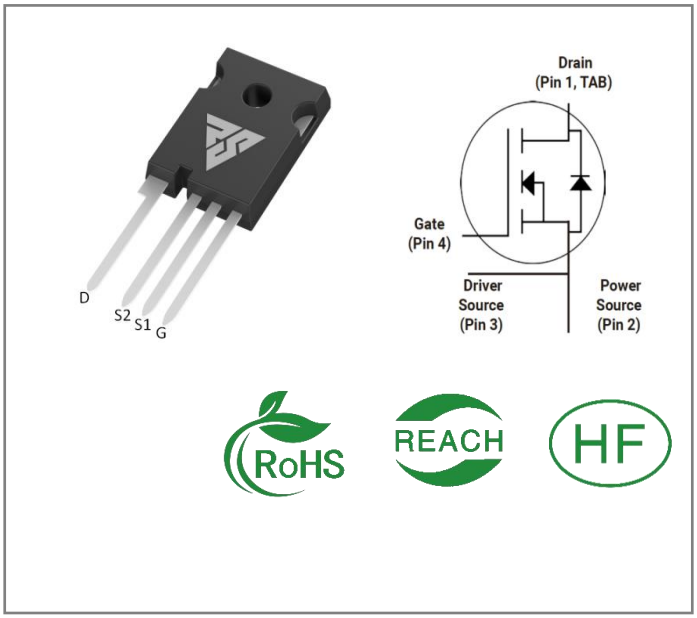
VDS	RDS(on)	ID@25℃
1700V	45mΩ	72A



Applications:

- Solar Inverters
- Switch Mode Power Supplies
- High Voltage DC/DC Converters
- EV Charging
- Motor Drives

Features:

- High Blocking Voltage with Low On-Resistance
- High Speed Switching with Low Capacitances
- Easy to Parallel and Simple to Drive
- Avalanche Ruggedness

Benefits:

- Higher System Efficiency
- Reduced Cooling Requirements
- Increased Power Density
- Increased System Switching Frequency

Ordering Information

Part Number	Package	Marking	Packing	Qty.
RSM170045Z	TO-247-4	RSM170045Z	Tube	30 PCS

Maximum Ratings （TJ= 25℃ unless otherwise specified）

Symbol	Parameter	Value	Unit	Test Conditions	Note
VDSmax	Drain - Source Voltage	1700	V	VGS=0V,ID =100μA	
VGSmax	Gate - Source Voltage	-10/+25	V	Absolute maximum values	
VGSop	Gate - Source Voltage	-5/+20	V	Recommended operational values	
ID	Continuous Drain Current	72 48	A	VGS=20V, TC =25℃ VGS=20V, TC =100℃	
ID(pulse)	Pulsed Drain Current	160	A	Pulse width tp limited by TJmax	
PD	Power Dissipation	520	W	TC =25℃， TJ =150℃	
TL	Solder Temperature	260	℃		
TJ, Tstg	Operating Junction and StorageTemperature	-40 to + 150	℃		

Electrical Characteristics (TJ= 25℃ unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions	Note
V(BR)DSS	Drain-Source Breakdown Voltage	1700			V	VGS=0V,ID =100μA	
VGS(th)	Gate Threshold Voltage	2.0	2.6	4.0	V	VGS= VDS, IDS=18mA, TC =25℃	
			1.8		V	VGS= VDS, IDS=18mA, TC =150℃	
IDSS	Zero Gate Voltage Drain Current		1	100	μA	VDS= 1700V, VGS=0V	
IGSS	Gate-Source Leakage Current			250	nA	VGS=25V, VDS= 0V	
RDS(on)	Drain-Source on-state Resistance		45	70	mΩ	VGS=20V, ID =50A, TC =25℃	
			90			VGS=20V, ID =50A, TC =150℃	
Ciss	Input Capacitance		3550		pF	VGS=0V, VDS=1000 V, f=1MHz，VAC=25 mV	
Coss	Output Capacitance		165				
Crss	Reverse Transfer Capacitance		6.1				
EON	Turn-On Switching Energy		3100		μJ	VDS =1200V, VGS =-5/20V,ID = 30A, RG(ext) = 2.5Ω, L= 200μH	
EOFF	Turn-Off Energy		1100				
td(on)	Turn-On Delay Time		27		ns	VDS =1200V, VGS =-5/20 V ID = 30A, RG(ext) =2. 5 Ω , RL =20Ω	
tr	Rise Time		32				
td(off)	Turn-Off Delay Time		16				
tf	Fall Time		10				
RG(int)	Internal Gate Resistance		2.6		Ω	f=1 MHz, VAC=25mV	
Qgs	Gate to Source Charge		54		nC	VDS=1200V, VGS=-5/20V ID =50A	
Qgd	Gate to Drain Charge		25		nC		
Qg	Total Gate Charge		193				

Reverse Diode Characteristics (TJ= 25℃ unless otherwise specified)

Symbol	Parameter	Typ.	Max	Unit	Test Conditions	Note
VSD	Diode Forward Voltage	3.6		V	VGS=-5V, ISD = 25 A, TJ = 25℃	
		3.3		V	VGS=-5V, ISD= 25 A, TJ= 150℃	
IS	Continuous Diode Forward Current		72	A	VGS=-5V,TC= 25℃	
trr	Reverse Recovery time	55		ns	ISD= 50A, VR = 1200V	
Qrr	Reverse Recovery Charge	220		nC		
Irrm	Peak Reverse Recovery Current	6.7		A		

Thermal Characteristics (TJ= 25℃ unless otherwise specified)

Symbol	Parameter	Typ.	Unit	Test Conditions	Note
RθJC	Thermal Resistance from Junction to Case	0.24	℃/W		
RθJA	Thermal Resistance From Junction to Ambient	40			

Typical Feature Curve

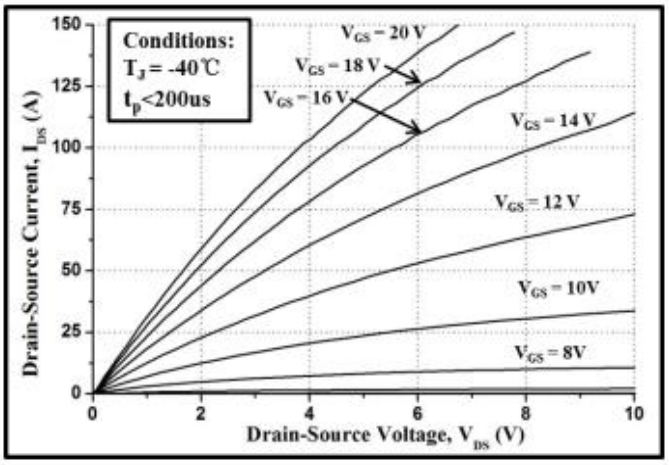


Figure 1. Output Characteristics T_J= -40 °C

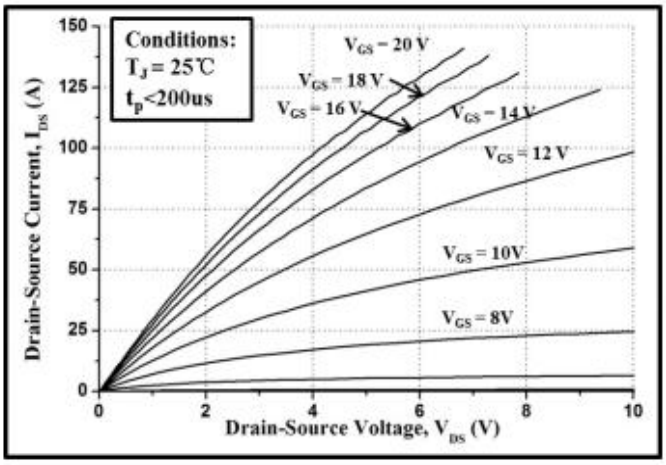


Figure 2. Output Characteristics T_J= 25 °C

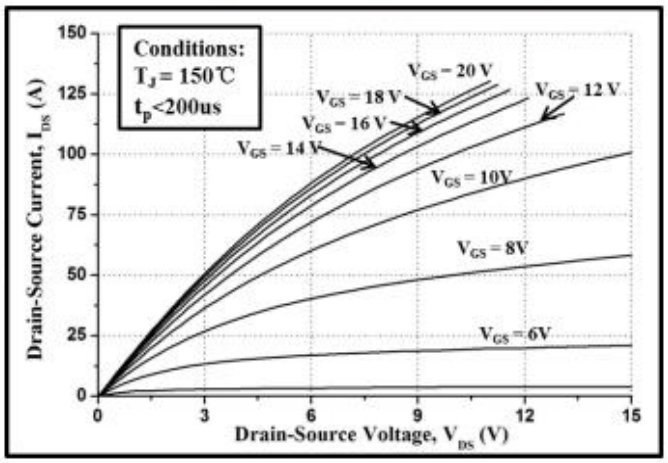


Figure 3. Output Characteristics T_J = 150 °C

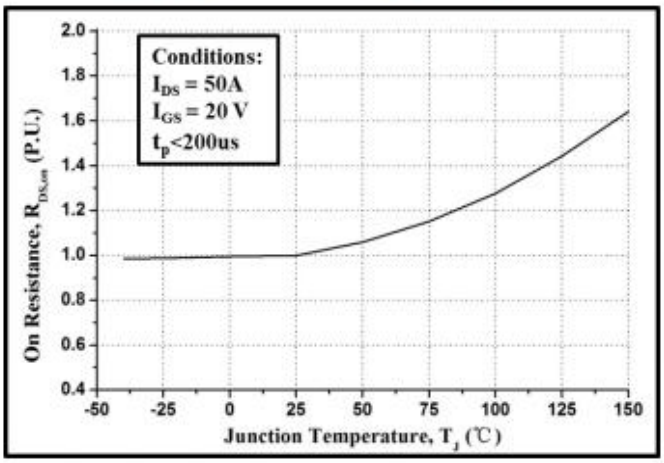


Figure 4. Normalized On-Resistance vs. Temperature

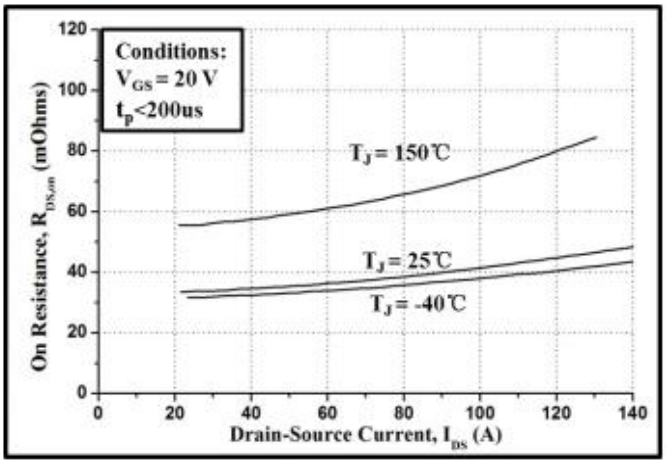


Figure 5. On-Resistance vs. Drain Current
For Various Temperatures

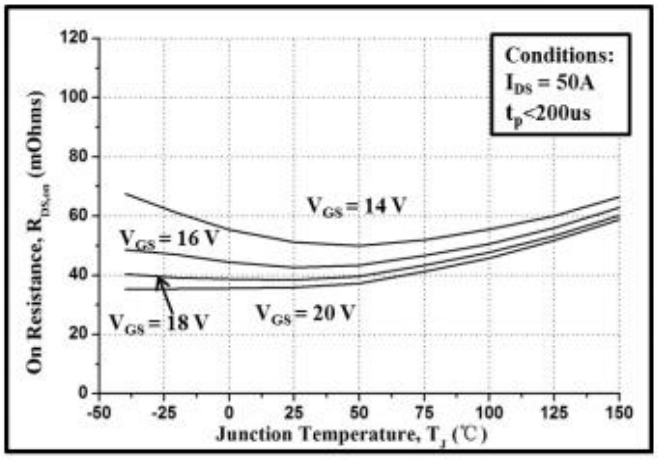


Figure 6. On-Resistance vs. Temperature
For Various Gate Voltage

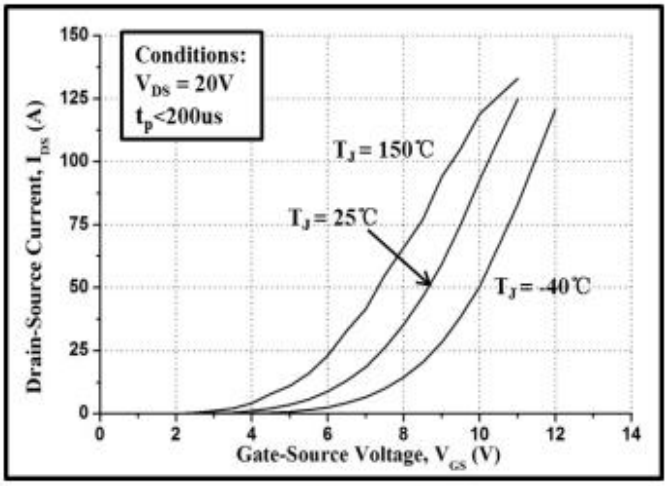


Figure 7. Transfer Characteristic for Various Junction Temperatures

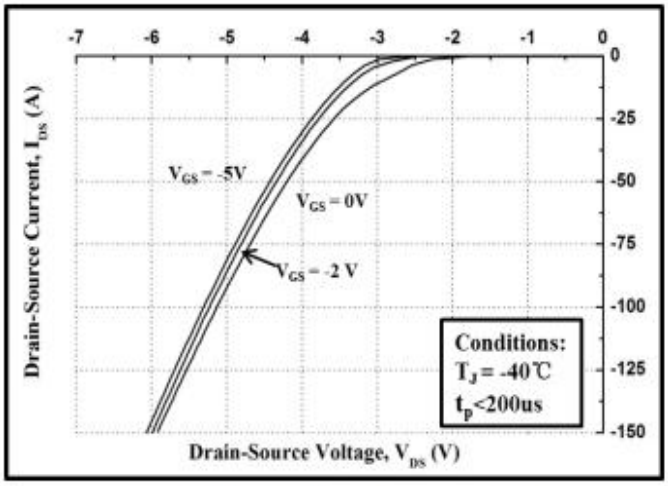


Figure 8. Body Diode Characteristic at -40 °C

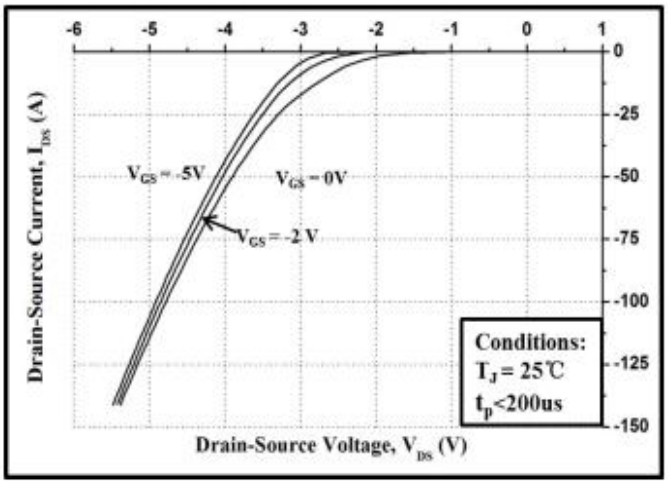


Figure 9. Body Diode Characteristic at 25 °C

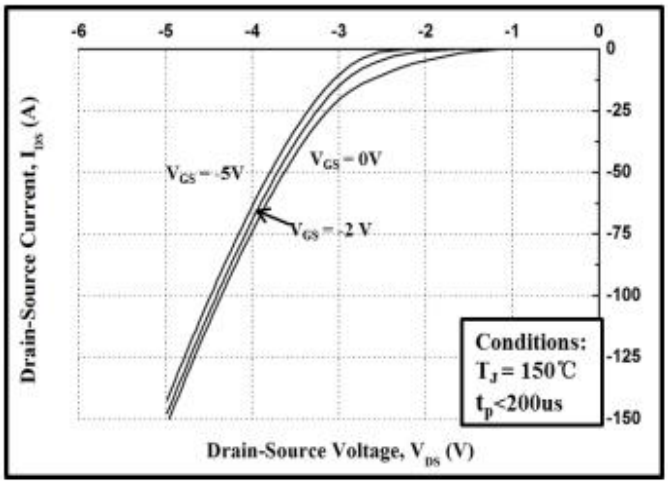


Figure 10. Body Diode Characteristic at 150 °C

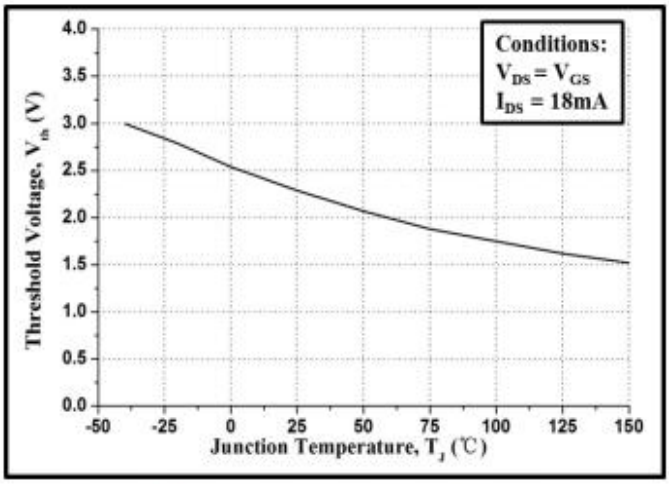


Figure 11. Threshold Voltage vs. Temperature

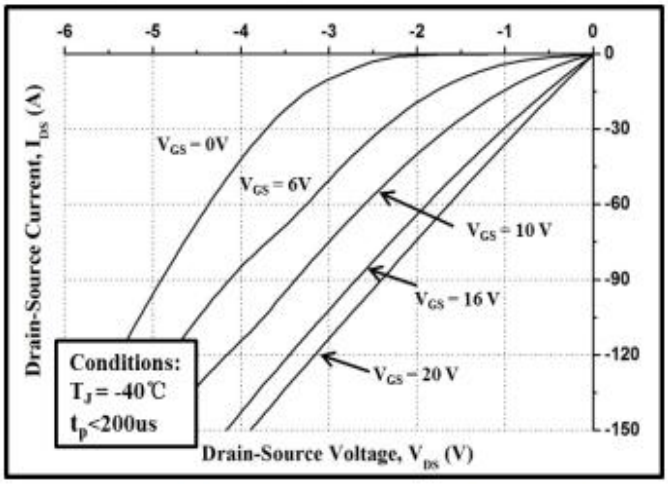


Figure 12. 3rd Quadrant Characteristic at -40 °C

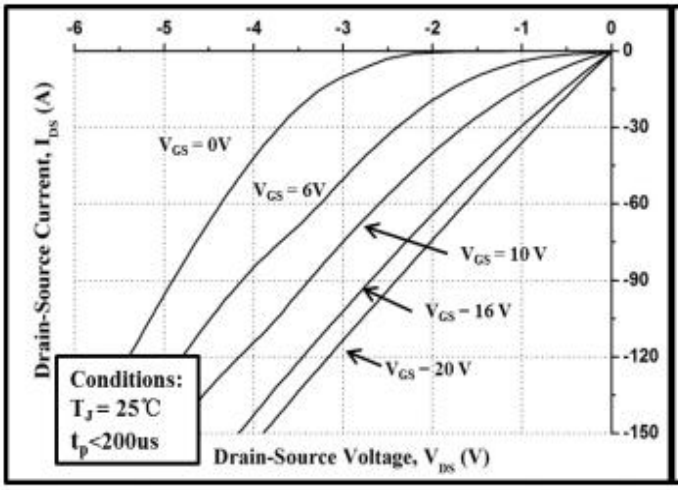


Figure 13. 3rd Quadrant Characteristic at 25°C

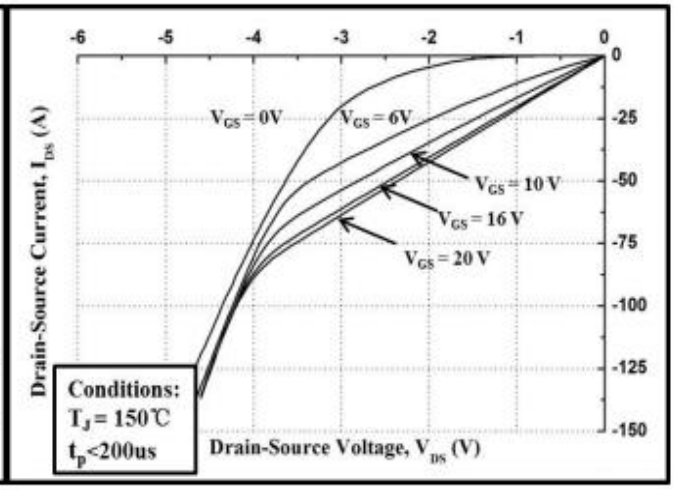


Figure 14. 3rd Quadrant Characteristic at 150 °C

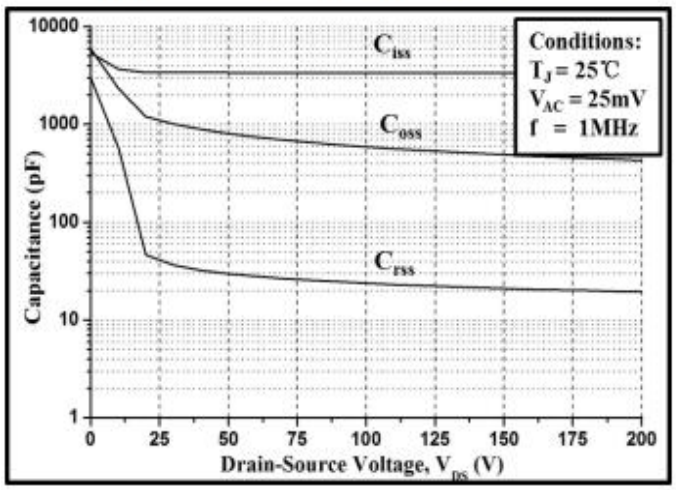


Figure 15. Capacitances vs. Drain-Source Voltage (0 - 200V)

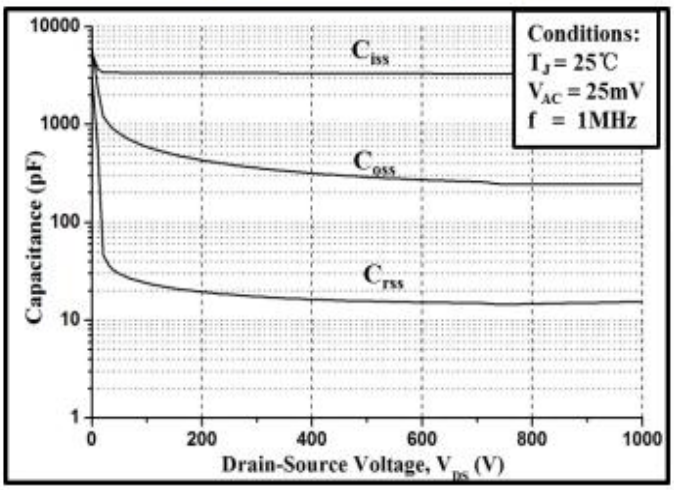


Figure 16. Capacitances vs. Drain-Source Voltage (0 - 1000V)

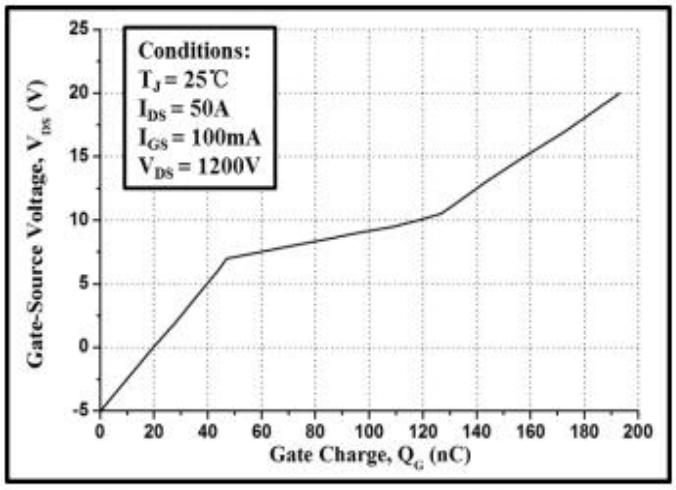


Figure 17. Gate Charge Characteristic

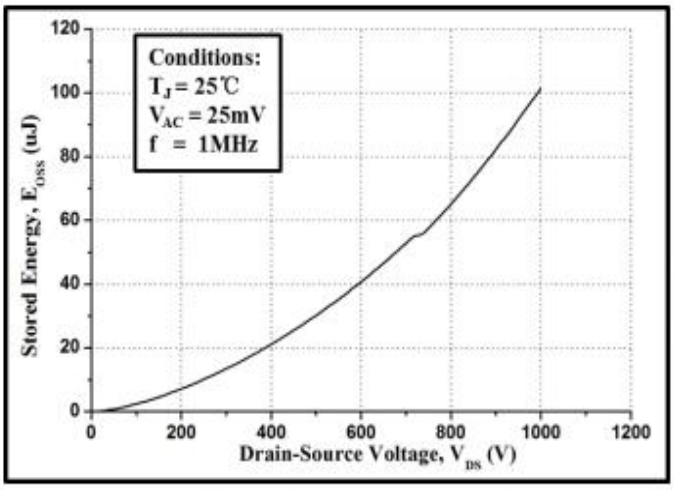
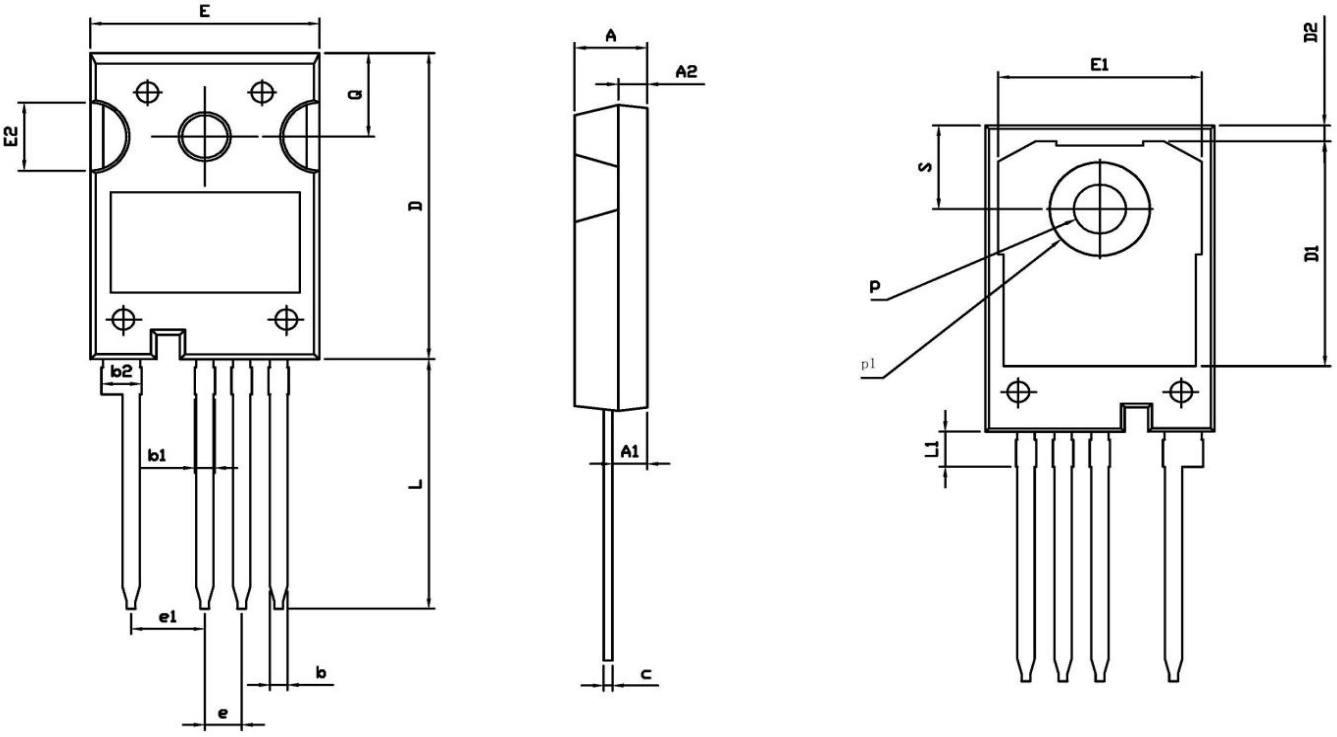
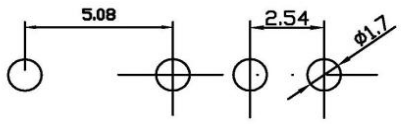


Figure 18. Output Capacitor Stored Energy

Package outline drawing(TO-247-4 Unit: mm)



RECOMMENDED LAND PATTERN



UNIT: mm

	MIN	NOM	MAX
A	4.80	5.00	5.20
A1	2.25	2.40	2.45
A2	1.85	2.00	2.15
b	1.05	1.20	1.35
b1	1.00	1.30	1.60
b2	2.35	2.65	2.95
c	0.50	0.60	0.70
D	22.34	22.54	22.74
D1	16.00	16.50	17.00
D2	0.97	1.17	1.37
e	2.34	2.54	2.74
e1	4.88	5.08	5.28
E	15.60	15.80	16.00
E1	13.50	14.00	14.50
E2	4.80	5.00	5.20
L	18.08	18.38	18.68
L1	2.38	2.58	2.78
p	3.50	3.60	3.70
p1	6.60	6.80	7.00
Q	6.00	6.15	6.30
S	6.00	6.15	6.30

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